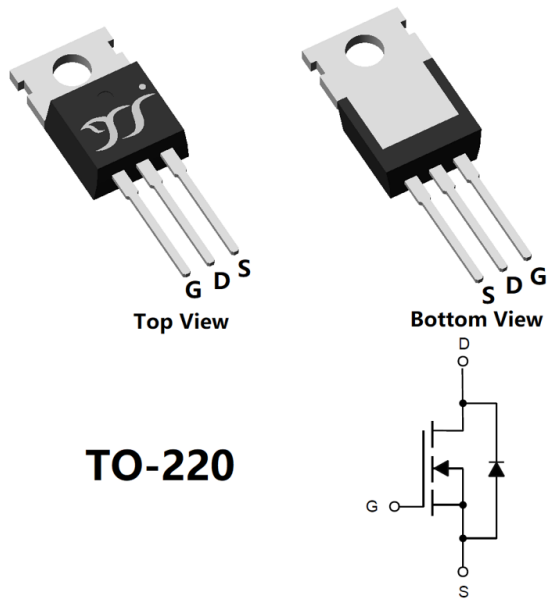


## N-Channel Enhancement Mode Field Effect Transistor



**TO-220**

### Product Summary

- $V_{DS}$  100V
- $I_D$  45A
- $R_{DS(ON)}$ ( at  $V_{GS}=10V$ ) <17 mohm
- 100% EAS Tested
- 100%  $\nabla V_{DS}$  Tested

### General Description

- Low  $R_{DS(on)}$  & FOM
- Extremely low switching loss
- Excellent stability and uniformity
- Fast switching and soft recovery
- Epoxy Meets UL 94 V-0 Flammability Rating
- Halogen Free

### Applications

- Power switching application
- Hard switched and high frequency circuits
- Uninterruptible power supply

### ■ Absolute Maximum Ratings ( $T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-source Voltage	$V_{DS}$	100	V
Gate-source Voltage	$V_{GS}$	$\pm 20$	V
Drain Current	$I_D$	$T_C=25^\circ\text{C}$	45
		$T_C=100^\circ\text{C}$	28.5
Pulsed Drain Current <sup>A</sup>	$I_{DM}$	220	A
Avalanche energy <sup>B</sup>	EAS	77	mJ
Total Power Dissipation <sup>C</sup>	$P_D$	$T_C=25^\circ\text{C}$	100
		$T_C=100^\circ\text{C}$	40
Junction and Storage Temperature Range	$T_J, T_{STG}$	-55~+150	$^\circ\text{C}$

### ■ Thermal resistance

Parameter	Symbol	Typ	Max	Units
Thermal Resistance Junction-to-Ambient <sup>D</sup>	$R_{\theta JA}$	12	15	$^\circ\text{C/W}$
Thermal Resistance Junction-to-Ambient <sup>D</sup>		Steady-State	50	
Thermal Resistance Junction-to-Case	$R_{\theta JC}$	1.0	1.25	

### ■ Ordering Information (Example)

PREFERRED P/N	PACKING CODE	Marking	MINIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
YJP45G10B	B1	YJP45G10B	50	/	5000	Tube



# YJP45G10B

## ■ Electrical Characteristics (T<sub>j</sub>=25°C unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
<b>Static Parameter</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> = 0V, I <sub>D</sub> =250μA	100			V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =100V, V <sub>GS</sub> =0V			1	μA
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> = ±20V, V <sub>DS</sub> =0V			±100	nA
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> =250μA	2	2.8	4	V
Static Drain-Source On-Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10V, I <sub>D</sub> =20A		14	17	mΩ
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> =20A, V <sub>GS</sub> =0V			1.3	V
Maximum Body-Diode Continuous Current	I <sub>S</sub>				45	A
Gate resistance	R <sub>G</sub>	f= 1 MHz, Open drain		1.2		Ω
<b>Dynamic Parameters</b>						
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =50V, V <sub>GS</sub> =0V, f=1MHZ		1135		pF
Output Capacitance	C <sub>oss</sub>			399		
Reverse Transfer Capacitance	C <sub>rss</sub>			18		
<b>Switching Parameters</b>						
Total Gate Charge	Q <sub>g</sub>	V <sub>GS</sub> =10V, V <sub>DS</sub> =50V, I <sub>D</sub> =25A		16		nC
Gate-Source Charge	Q <sub>gs</sub>			5.6		
Gate-Drain Charge	Q <sub>gd</sub>			2.4		
Reverse Recovery Charge	Q <sub>rr</sub>	I <sub>F</sub> =20A, di/dt=100A/us		42		ns
Reverse Recovery Time	t <sub>rr</sub>			39.8		
Turn-on Delay Time	t <sub>D(on)</sub>	V <sub>GS</sub> =10V, V <sub>DD</sub> =50V, I <sub>D</sub> =25A R <sub>GEN</sub> =2.2Ω		39.2		ns
Turn-on Rise Time	t <sub>r</sub>			11		
Turn-off Delay Time	t <sub>D(off)</sub>			53.2		
Turn-off fall Time	t <sub>f</sub>			15.8		

A. Repetitive rating; pulse width limited by max. junction temperature.

B. V<sub>DD</sub>=50V, R<sub>G</sub>=25Ω, L=0.5mH, I<sub>AS</sub>=17.5A,.

C. Pd is based on max. junction temperature, using junction-case thermal resistance.

D. The value of R<sub>qJA</sub> is measured with the device mounted on 1in2 FR-4 board with 2oz. Copper, in a still air environment with T<sub>A</sub> =25 C. The Power dissipation PDSM is based on R<sub>qJA</sub> ≤ 10s and the maximum allowed junction temperature of 150 C. The value in any given application depends on the user's specific board design.



## Typical Performance Characteristics

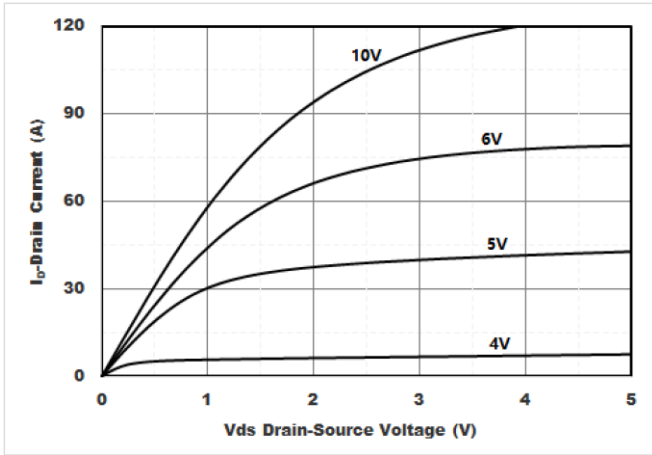


Figure1. Output Characteristics

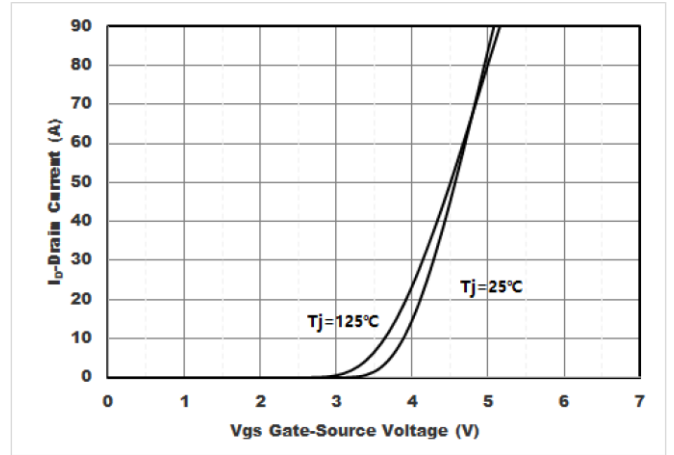


Figure2. Transfer Characteristics

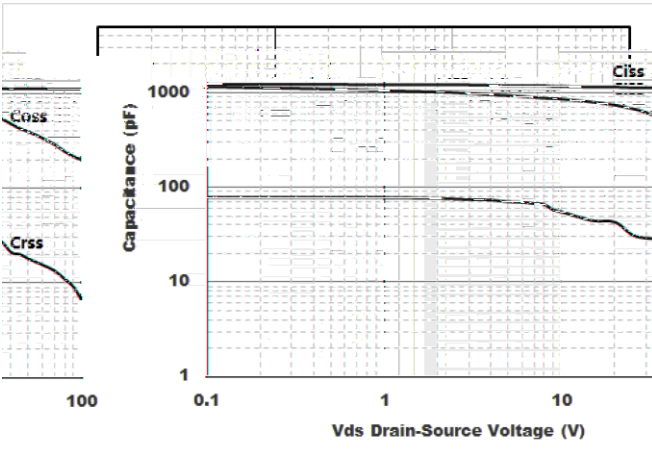


Figure3. Capacitance Characteristics

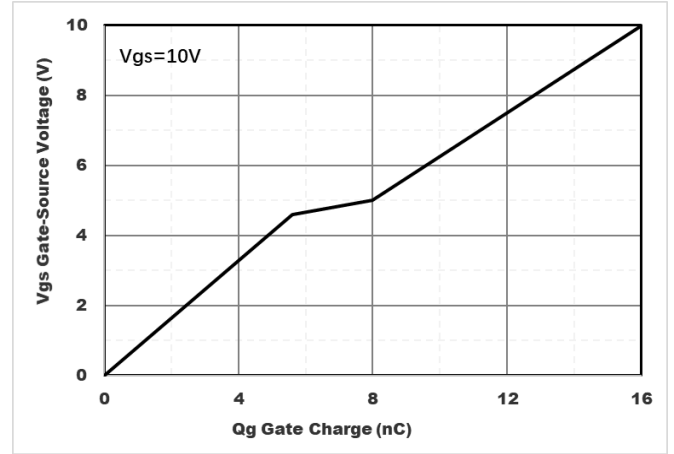


Figure4. Gate Charge

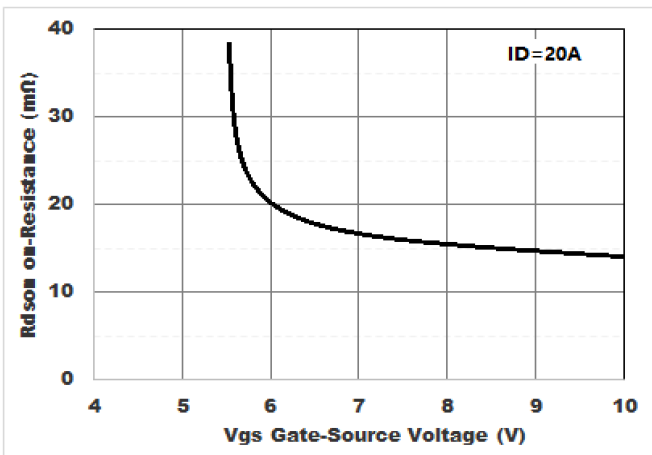


Figure5. : On-Resistance vs. Drain Current and Gate Voltage

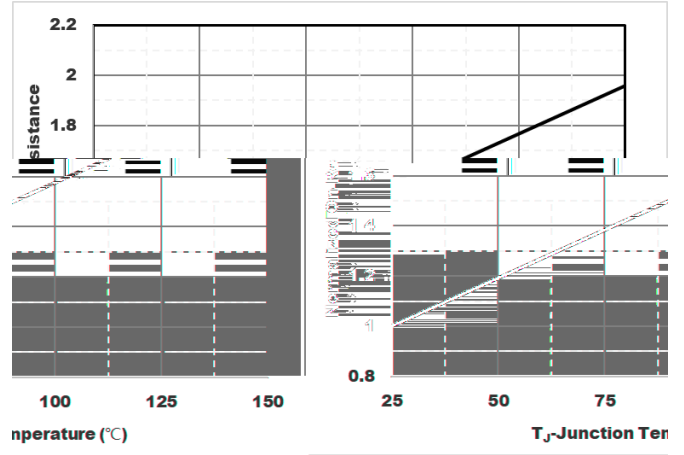


Figure6. Normalized On-Resistance

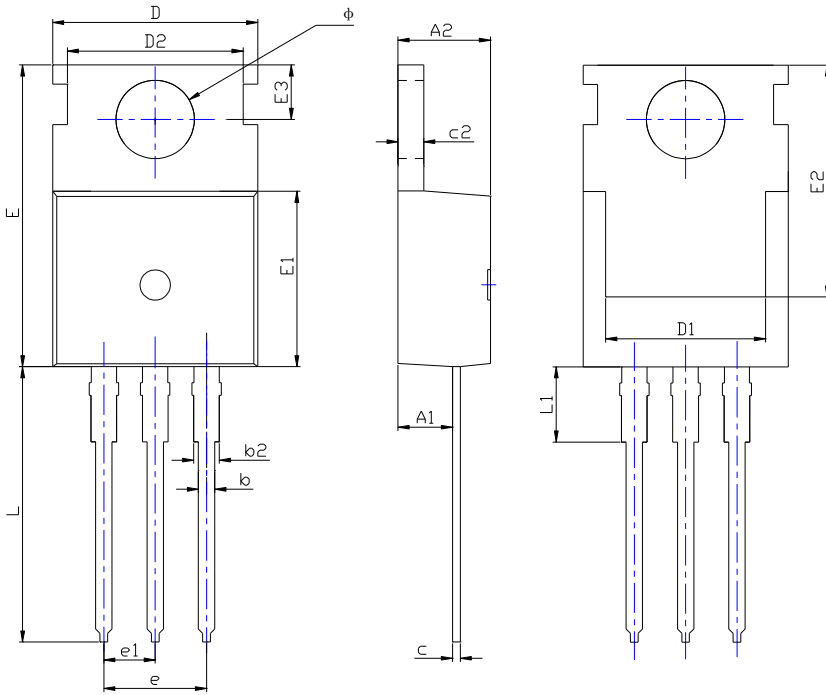
**YJP45G10B**

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# YJP45G10B

## ■ TO-220AB-C Package information



SYMBOL	DIMENSIONS			
	INCHES		Millimeter	
	MIN.	MAX.	MIN.	MAX.
A1	0.091	0.098	2.300	2.500
A2	0.173	0.181	4.400	4.600
b	0.028	0.035	0.700	0.900
b2	0.049	0.056	1.250	1.420
c	0.018	0.022	0.450	0.550
c2	0.049	0.053	1.250	1.350
D	0.382	0.402	9.700	10.200
D1	0.295	0.331	7.500	8.400
D2	0.335	0.350	8.500	8.900
E	0.602	0.634	15.300	16.100
E1	0.358	0.366	9.100	9.300
E2	0.497	0.525	12.630	13.330
E3	0.108BSC		2.750BSC	
e	0.200BSC		5.080BSC	
e1	0.100BSC		2.540BSC	
L	0.512	0.531	13.000	13.500
L1	---	0.138	---	3.500
$\phi$	0.140	0.148	3.550	3.750

NOTE:  
1. PACKAGE BODY SIZES EXCLUDE MOLD FLASH AND GATE BURRS.  
2. TOLERANCE 0.1mm UNLESS OTHERWISE SPECIFIED.



## YJP45G10B

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